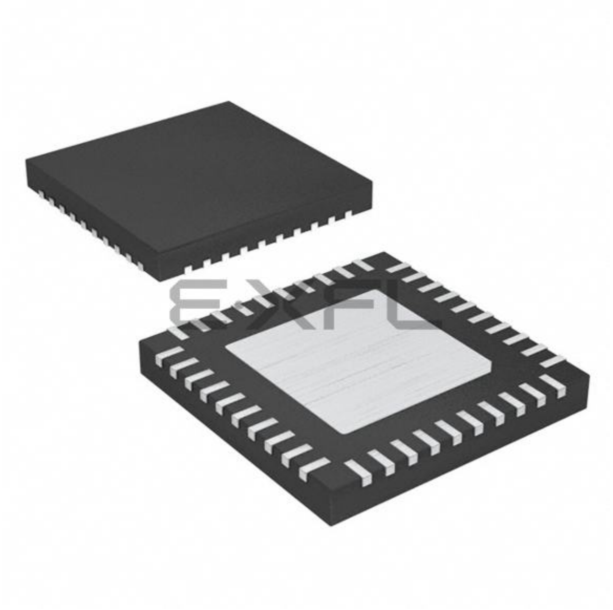
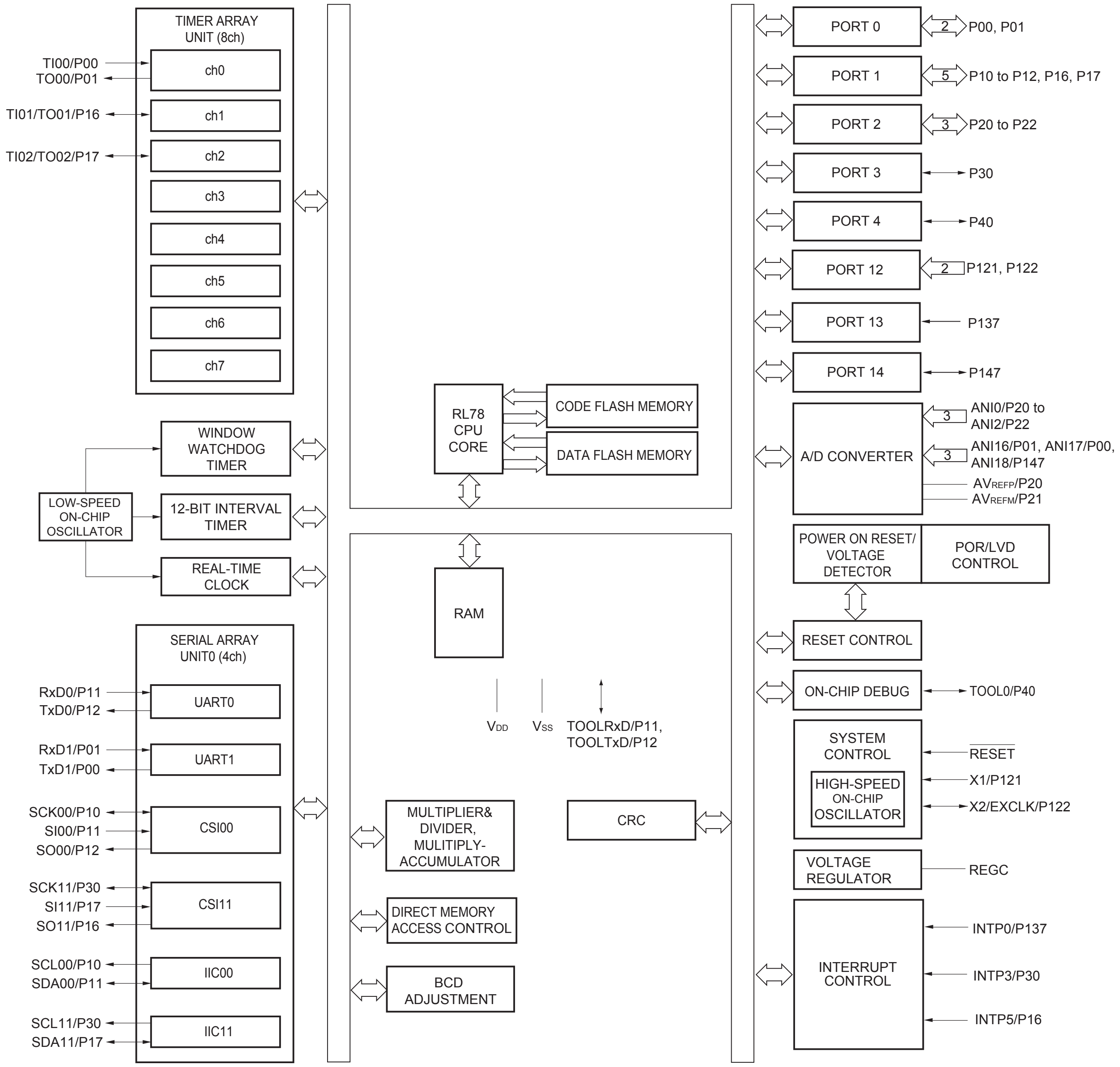


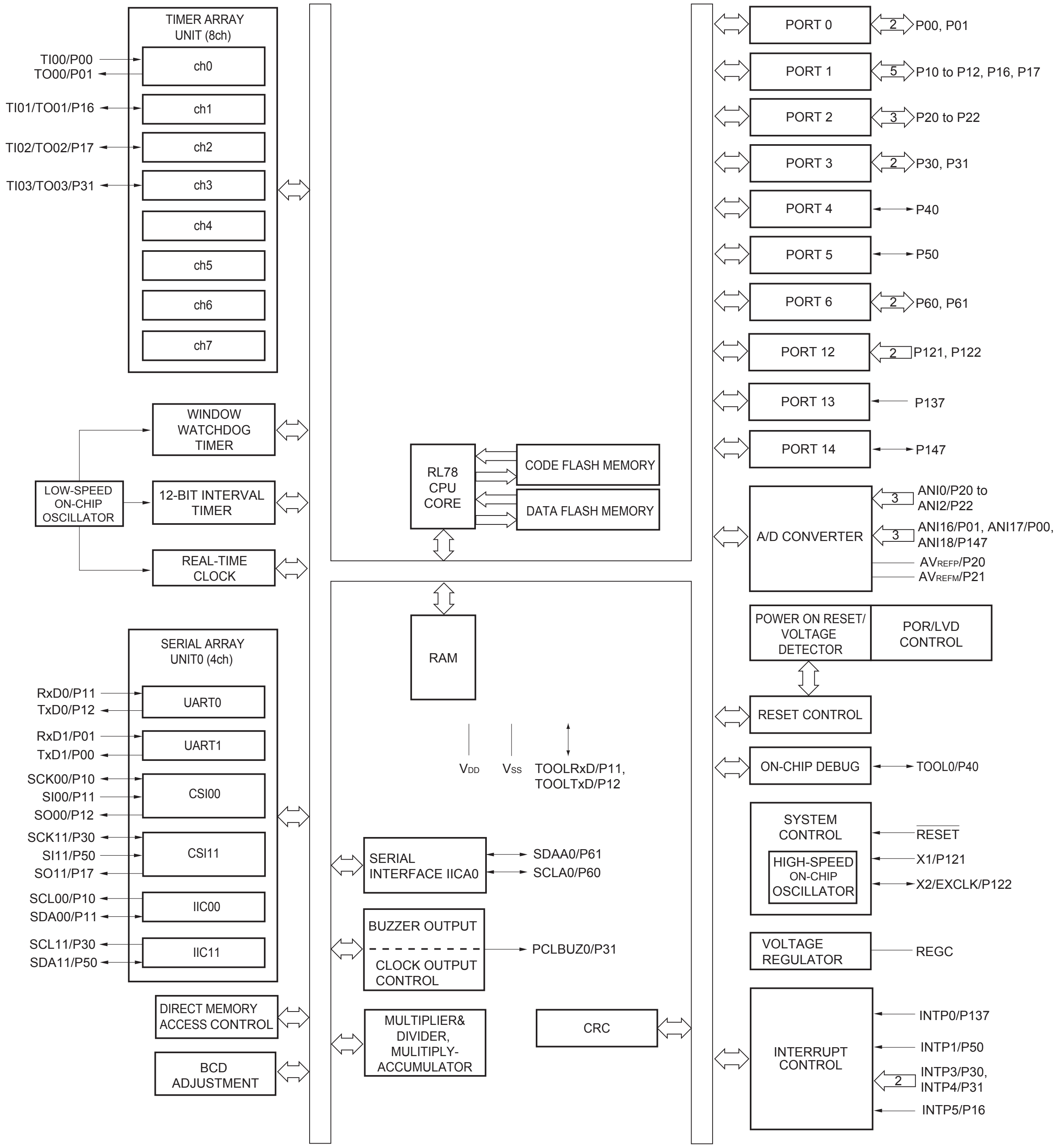
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	40-WFQFN Exposed Pad
Supplier Device Package	40-HWQFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101eaana-u0

1.5 Block Diagram

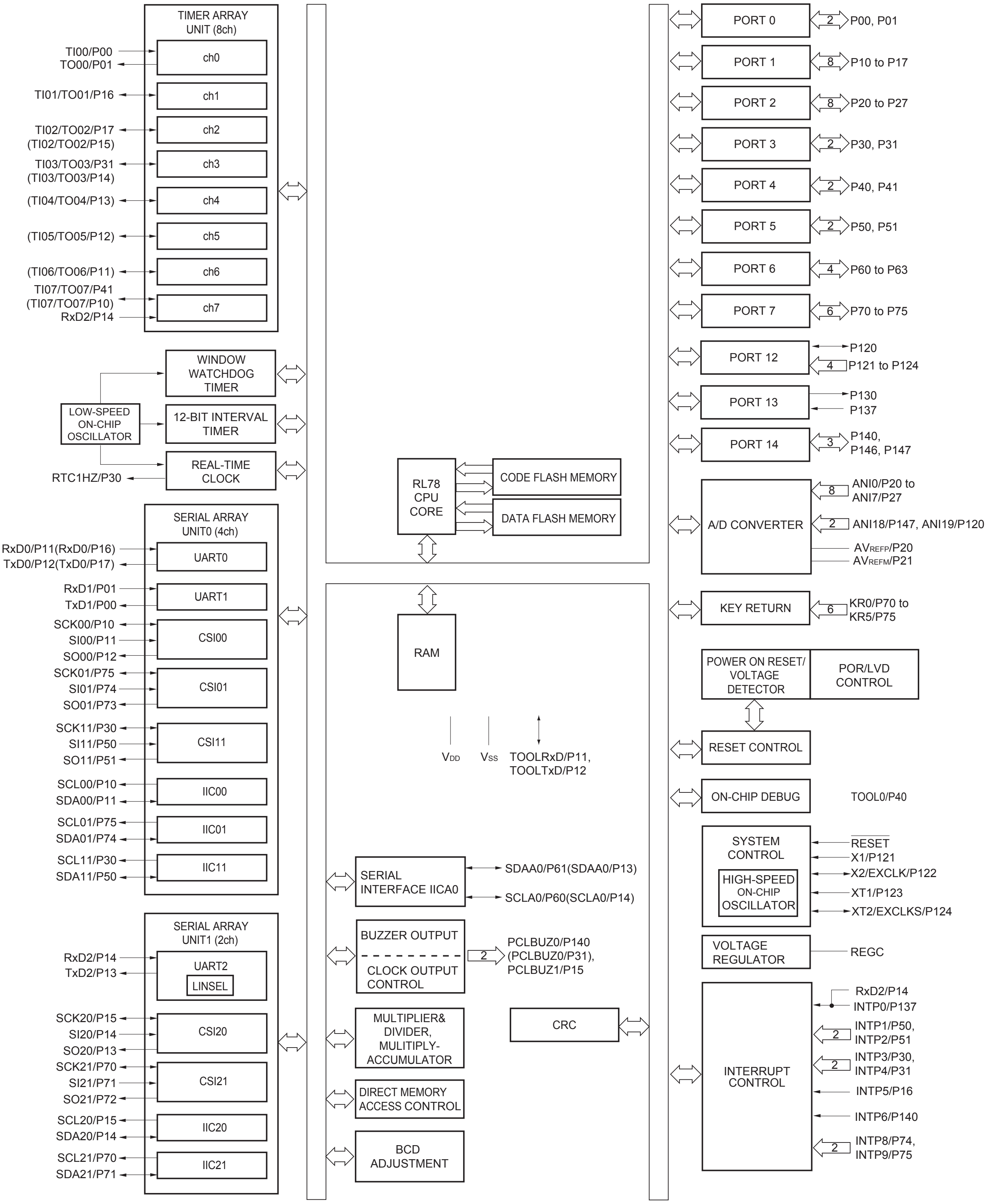
1.5.1 20-pin products



1.5.2 24-pin products

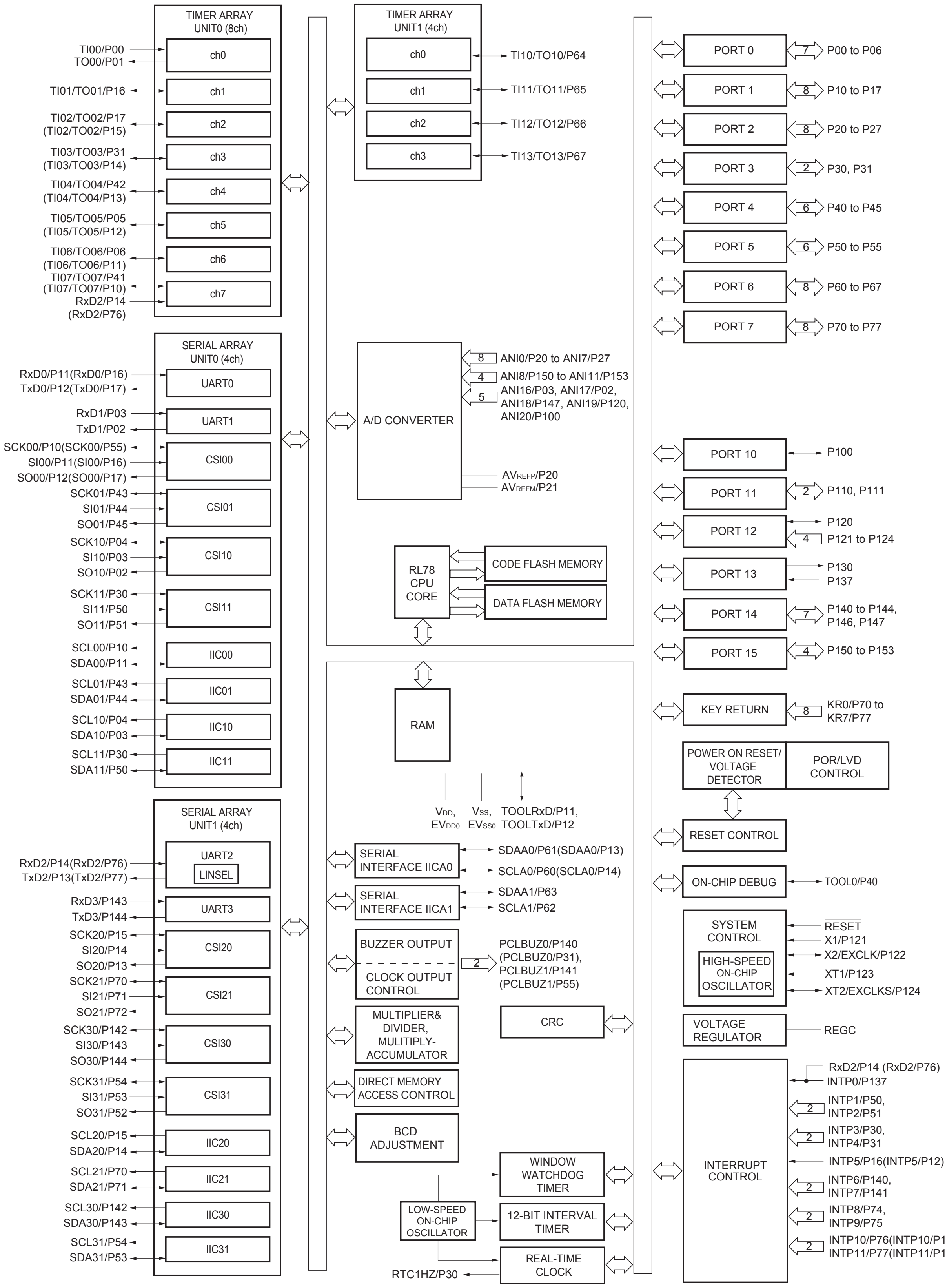


1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	−40	mA
		Total of all pins −170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	−70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	−100	mA
	I_{OH2}	Per pin	P20 to P27, P150 to P156	−0.5	mA
		Total of all pins		−2	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	I_{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A	In normal operation mode		−40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			−65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

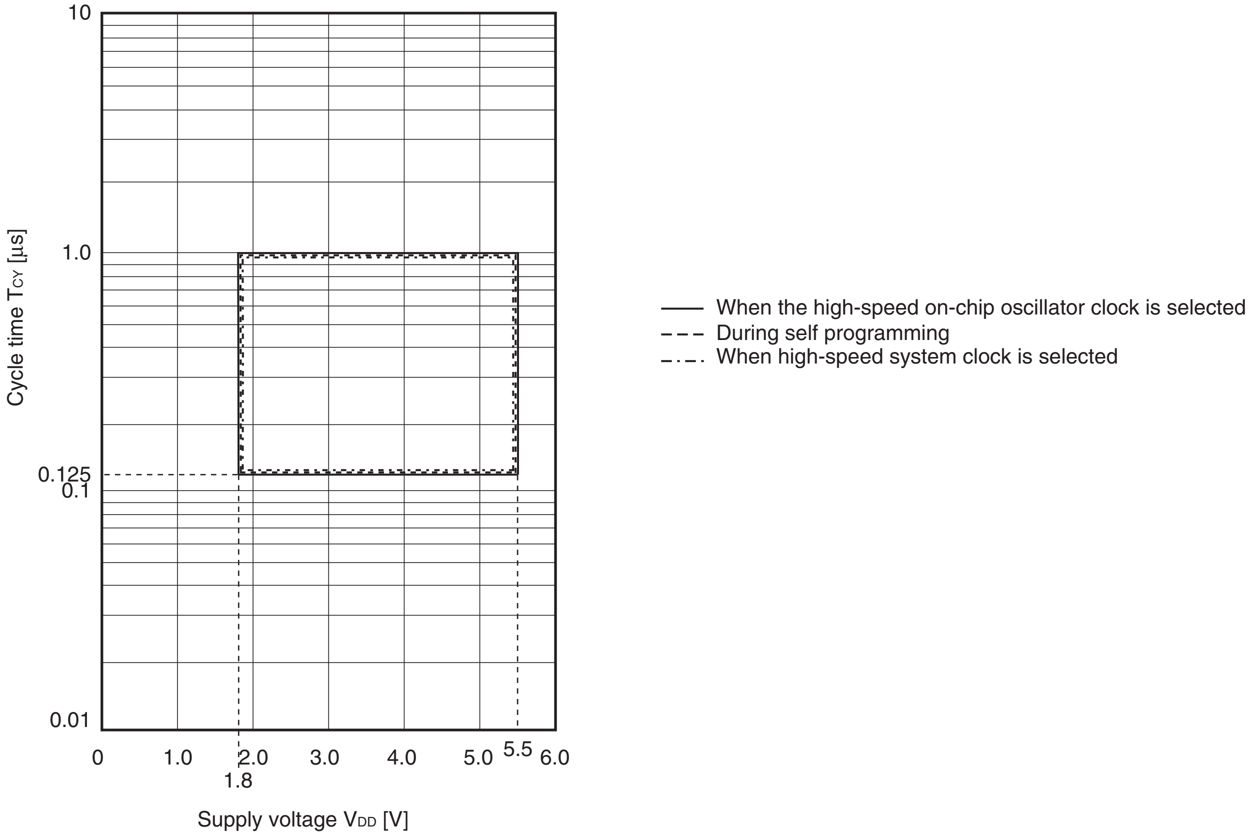
(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

(T_A = −40 to +85°C, 1.6 V $\leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V) (1/2)

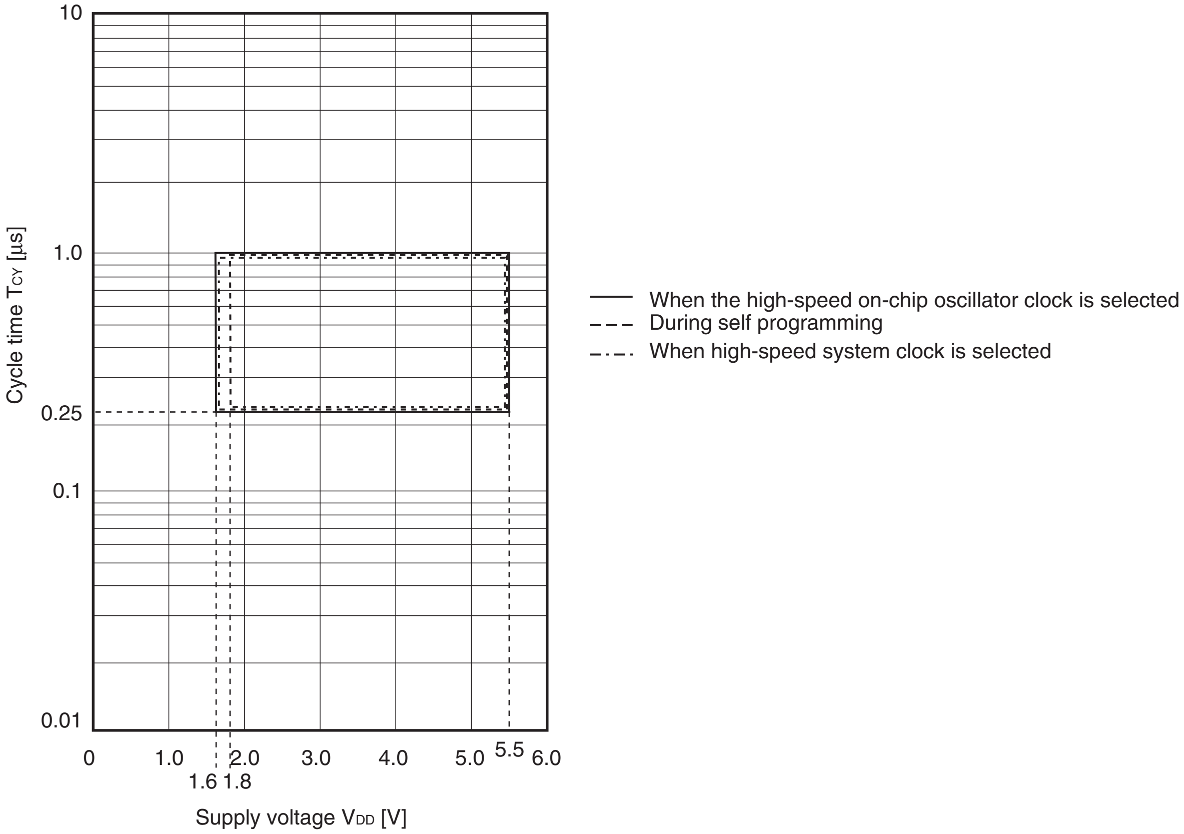
Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD1}	Operating mode	HS (high-speed main) mode [Note 5]	f_{IH} = 32 MHz [Note 3]	Basic operation	V_{DD} = 5.0 V		2.6		mA
						V_{DD} = 3.0 V		2.6		mA
					Normal operation	V_{DD} = 5.0 V		6.1	9.5	mA
						V_{DD} = 3.0 V		6.1	9.5	mA
				f_{IH} = 24 MHz [Note 3]	Normal operation	V_{DD} = 5.0 V		4.8	7.4	mA
						V_{DD} = 3.0 V		4.8	7.4	mA
				f_{IH} = 16 MHz [Note 3]	Normal operation	V_{DD} = 5.0 V		3.5	5.3	mA
						V_{DD} = 3.0 V		3.5	5.3	mA
			LS (low-speed main) mode [Note 5]	f_{IH} = 8 MHz [Note 3]	Normal operation	V_{DD} = 3.0 V		1.5	2.3	mA
						V_{DD} = 2.0 V		1.5	2.3	mA
			LV (low-voltage main) mode [Note 5]	f_{IH} = 4 MHz [Note 3]	Normal operation	V_{DD} = 3.0 V		1.5	2.0	mA
						V_{DD} = 2.0 V		1.5	2.0	mA
			HS (high-speed main) mode [Note 5]	f_{MX} = 20 MHz [Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		3.9	6.1	mA
						Resonator connection		4.1	6.3	mA
				f_{MX} = 20 MHz [Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		3.9	6.1	mA
						Resonator connection		4.1	6.3	mA
				f_{MX} = 10 MHz [Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		2.5	3.7	mA
						Resonator connection		2.5	3.7	mA
				f_{MX} = 10 MHz [Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		2.5	3.7	mA
						Resonator connection		2.5	3.7	mA
			LS (low-speed main) mode [Note 5]	f_{MX} = 8 MHz [Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		1.4	2.2	mA
						Resonator connection		1.4	2.2	mA
				f_{MX} = 8 MHz [Note 2], V_{DD} = 2.0 V	Normal operation	Square wave input		1.4	2.2	mA
						Resonator connection		1.4	2.2	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 4] T_A = −40°C	Normal operation	Square wave input		5.4	6.5	μA
						Resonator connection		5.5	6.6	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +25°C	Normal operation	Square wave input		5.5	6.5	μA
						Resonator connection		5.6	6.6	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +50°C	Normal operation	Square wave input		5.6	9.4	μA
						Resonator connection		5.7	9.5	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +70°C	Normal operation	Square wave input		5.9	12.0	μA
						Resonator connection		6.0	12.1	μA
				f_{SUB} = 32.768 kHz [Note 4] T_A = +85°C	Normal operation	Square wave input		6.6	16.3	μA
						Resonator connection		6.7	16.4	μA

(**Notes** and **Remarks** are listed on the next page.)

T_{CY} vs V_{DD} (LS (low-speed main) mode)



T_{CY} vs V_{DD} (LV (low-voltage main) mode)



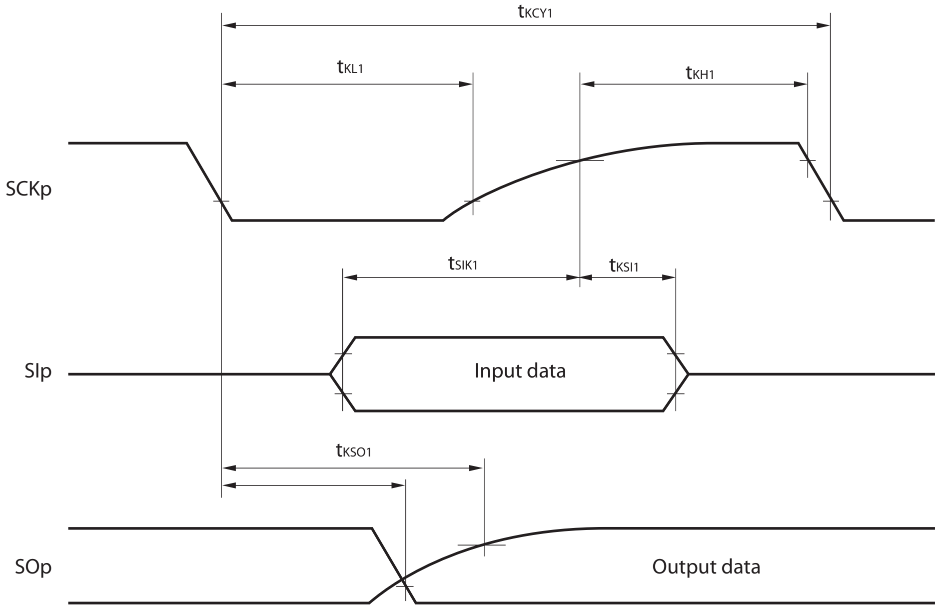
(5) During communication at same potential (simplified I^2C mode) (1/2)

(T_A = −40 to +85°C, $1.6\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

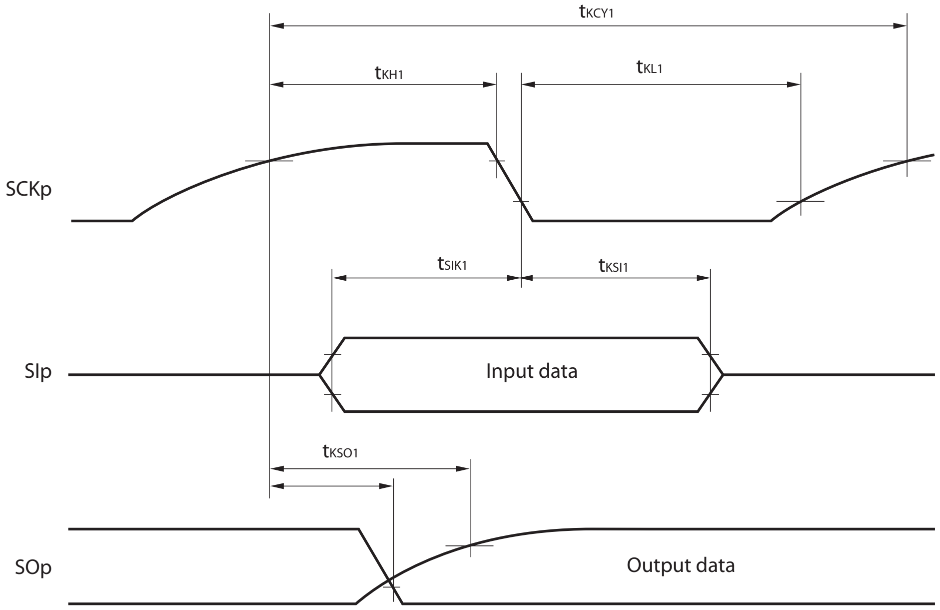
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100\ pF$, $R_b = 3\ k\Omega$		400 Note 1		400 Note 1		400 Note 1	kHz
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$		250 Note 1		250 Note 1		250 Note 1	kHz
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	475		1150		1150		ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100\ pF$, $R_b = 3\ k\Omega$	1150		1150		1150		ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	1550		1550		1550		ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	1850		1850		1850		ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	—		1850		1850		ns
Hold time when SCLr = "H"	t_{HIGH}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	475		1150		1150		ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100\ pF$, $R_b = 3\ k\Omega$	1150		1150		1150		ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	1550		1550		1550		ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	1850		1850		1850		ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	—		1850		1850		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = −40 to +85°C, $1.8\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$	$24\ MHz < f_{MCK}$	14/f_{MCK}		—		—		ns
			$20\ MHz < f_{MCK} \le 24\ MHz$	12/f_{MCK}		—		—		ns
			$8\ MHz < f_{MCK} \le 20\ MHz$	10/f_{MCK}		—		—		ns
			$4\ MHz < f_{MCK} \le 8\ MHz$	8/f_{MCK}		16/f_{MCK}		—		ns
			$f_{MCK} \le 4\ MHz$	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$	$24\ MHz < f_{MCK}$	20/f_{MCK}		—		—		ns
			$20\ MHz < f_{MCK} \le 24\ MHz$	16/f_{MCK}		—		—		ns
			$16\ MHz < f_{MCK} \le 20\ MHz$	14/f_{MCK}		—		—		ns
			$8\ MHz < f_{MCK} \le 16\ MHz$	12/f_{MCK}		—		—		ns
			$4\ MHz < f_{MCK} \le 8\ MHz$	8/f_{MCK}		16/f_{MCK}		—		ns
			$f_{MCK} \le 4\ MHz$	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$ Note 2	$24\ MHz < f_{MCK}$	48/f_{MCK}		—		—		ns
			$20\ MHz < f_{MCK} \le 24\ MHz$	36/f_{MCK}		—		—		ns
			$16\ MHz < f_{MCK} \le 20\ MHz$	32/f_{MCK}		—		—		ns
			$8\ MHz < f_{MCK} \le 16\ MHz$	26/f_{MCK}		—		—		ns
			$4\ MHz < f_{MCK} \le 8\ MHz$	16/f_{MCK}		16/f_{MCK}		—		ns
			$f_{MCK} \le 4\ MHz$	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low[Note 1]	I_{OL1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 [Note 2]	mA
		Per pin for P60 to P63				15.0 [Note 2]	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% [Note 3])	4.0 V ≤ EV_{DD0} ≤ 5.5 V			40.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			15.0	mA
			2.4 V ≤ EV_{DD0} < 2.7 V			9.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% [Note 3])	4.0 V ≤ EV_{DD0} ≤ 5.5 V			40.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			35.0	mA
			2,4 V ≤ EV_{DD0} < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% [Note 3])				80.0	mA
	I_{OL2}	Per pin for P20 to P27, P150 to P156				0.4 [Note 2]	mA
		Total of all pins (When duty ≤ 70%[Note 3])	2,4 V ≤ V_{DD} ≤ 5.5 V			5.0	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EV_{SS0}, EV_{SS1} and V_{SS} pin.

2. Do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter is in operation.

7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

8. Current flowing only during data flash rewrite.

9. Current flowing only during self programming.

10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode** in the RL78/G13 User's Manual.

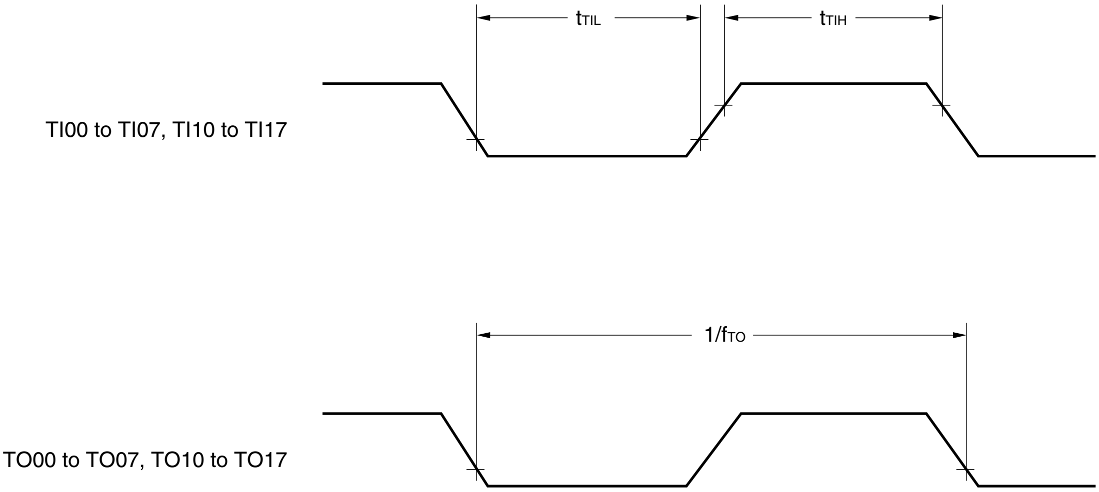
Remarks 1. f_{IL}: Low-speed on-chip oscillator clock frequency

2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

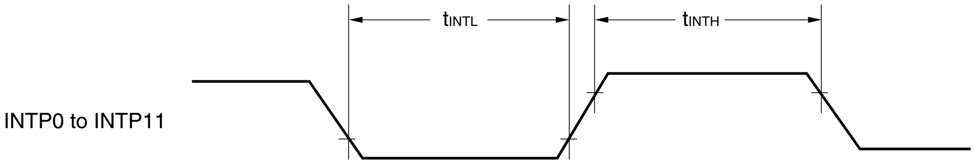
3. f_{CLK}: CPU/peripheral hardware clock frequency

4. Temperature condition of the TYP. value is T_A = 25°C

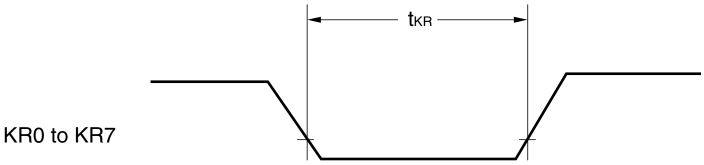
TI/TO Timing



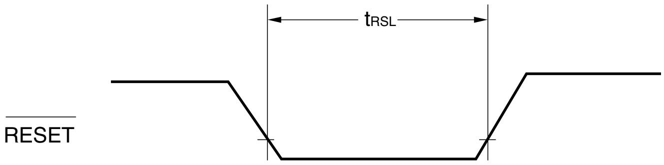
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			$f_{MCK}/12$ Note 1	bps
				Theoretical value of the maximum transfer rate f_{CLK} = 32 MHz, f_{MCK} = f_{CLK}		2.6	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			$f_{MCK}/12$ Note 1	bps
				Theoretical value of the maximum transfer rate f_{CLK} = 32 MHz, f_{MCK} = f_{CLK}		2.6	Mbps
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			$f_{MCK}/12$ Notes 1,2	bps
				Theoretical value of the maximum transfer rate f_{CLK} = 32 MHz, f_{MCK} = f_{CLK}		2.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when E_{VDD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

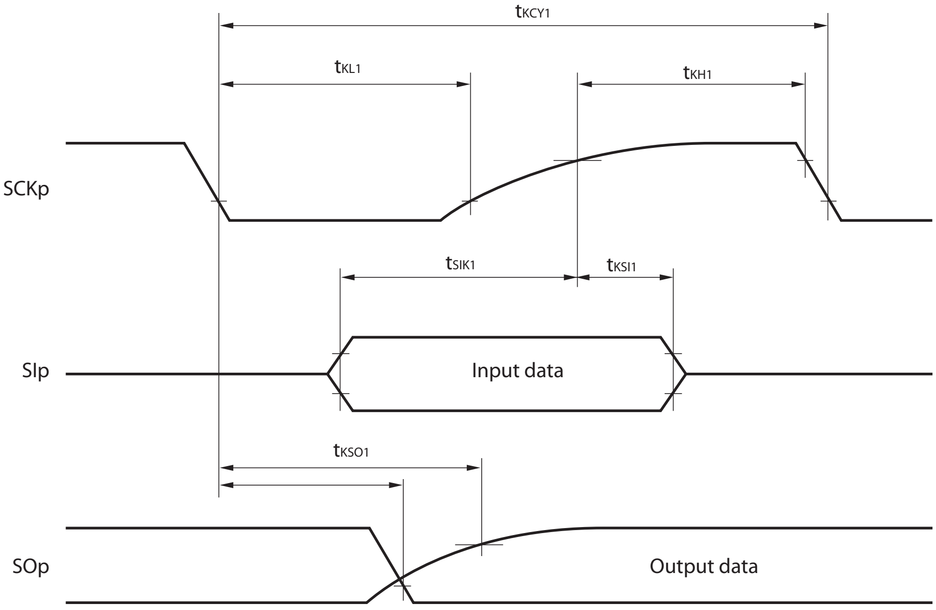
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	t_{SIK1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	88		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	38		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		50	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

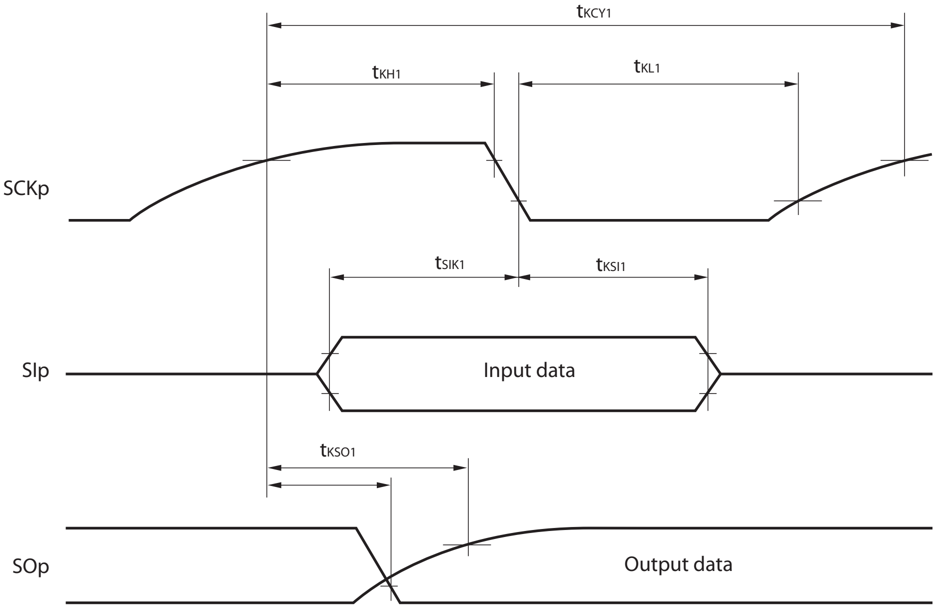
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI14	Refer to **3.6.1 (1)**.	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.
ANI16 to ANI26	Refer to **3.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **3.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Integral linearity error [Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage output (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

(**Notes** are listed on the next page.)

3.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

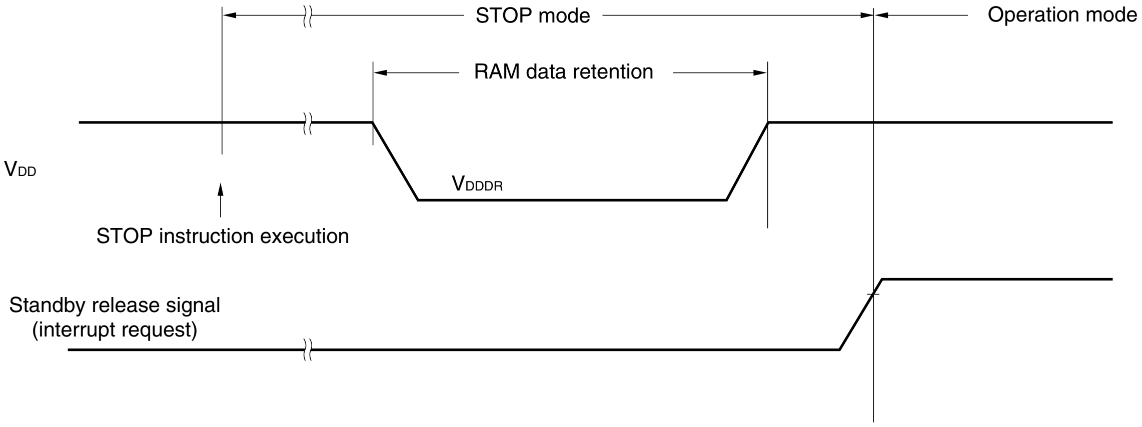
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44[Note]		5.5	V

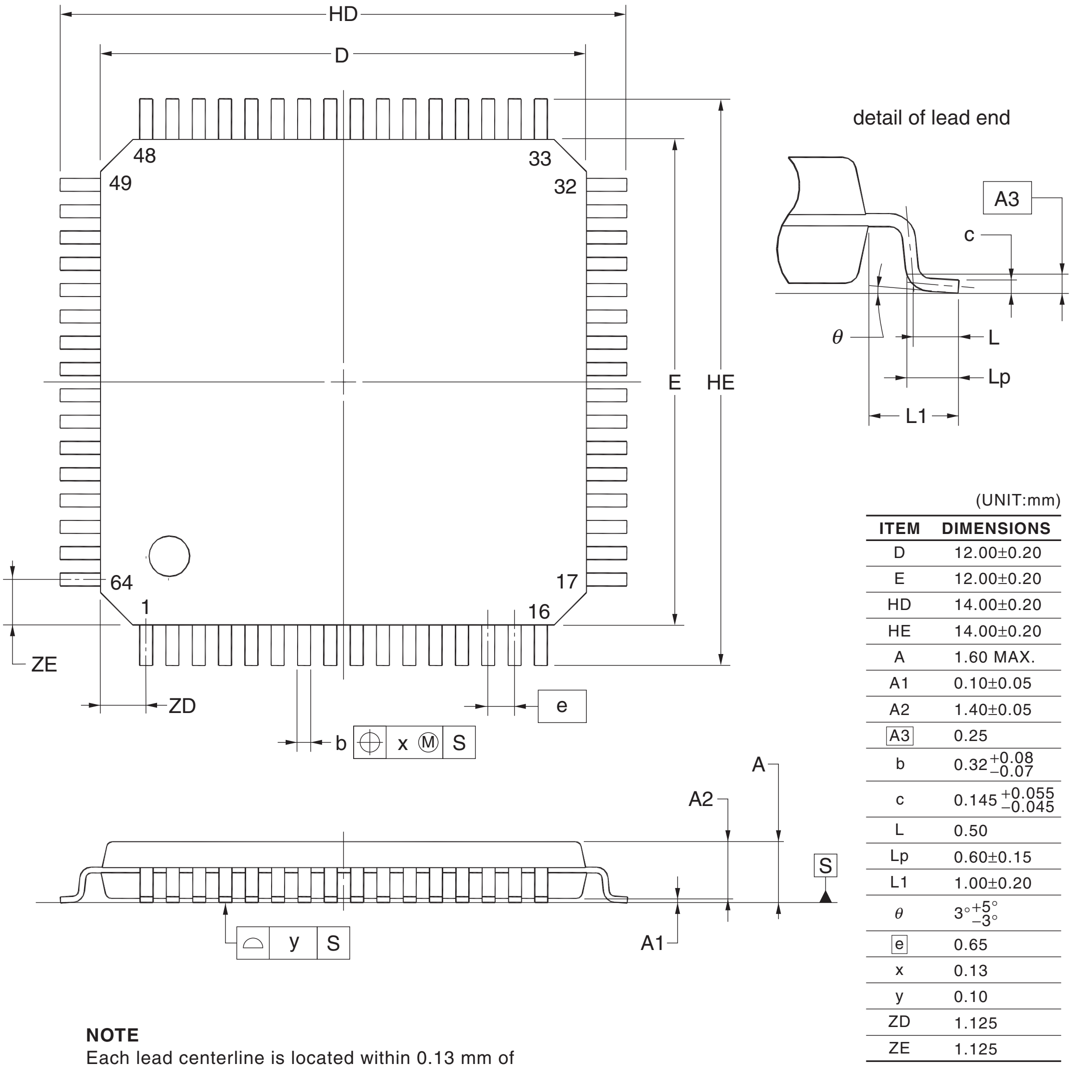
Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA
R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA
R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA
R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA
R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
$\boxed{A3}$	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
$\boxed{e}$	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.